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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT				APPLICA	Ha	Hammond et al.			
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		FILING DATE: March 10, 2004 GROUP: 2812							
U.S. PATENT DOCUMENTS									
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OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication) INIT.									
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ASC-057C1 ATTORNEY DOCKET NO.: **FORM PTO - 1449** · Hammond et al. SECOND SUPPLEMENTAL INFORMATION APPLICANT(S): **DISCLOSURE STATEMENT** SERIAL NO.: 10/797,231 FILING DATE: March 10, 2004 GROUP: 2812 U.S. PATENT DOCUMENTS EXAM. DOCUMENT DATE NAME CLASS SUB FILING DATE IF INIT. NUMBER **CLASS** APPROPRIATE A67 5,417,180 5/23/1995 Nakamura FOREIGN PATENT DOCUMENTS ENGLISH **DOCUMENT** DATE COUNTRY **CLASS** SUB **FILING** ABSTRACT EXAM. LANG INIT. NUMBER CODE CLASS-DATE ONLY (Y/N) OTHER ART, JOURNAL ARTICLES, ETC. OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication) EXAM. INIT. Chang, G.K., et al., "Selective Etching of SiGe on SiGe/Se Heterostructures," J. ELECTROCHEM. SOC. (1999) 138(1):202-04. Ismail, K., "Si/SiGe High-Speed Field Effect Transistors," IEEE IEDM TECH. DIG. (1995) 509-12. C75 C76 LeGoues, F.K. et al., "Oxidation studies of SiGe," J. APPL. PHYS. (1989) 65(4): 1724-28. Rhee, S.S., et al., "SiGe Resonant Tunneling Hot Carrier Transistor," IEEE IEDM TECH. DIG. (1999) 651-54. C78 Wolf, S., SILICON PROCESSING FOR THE VLSI ERA: VOL.2-PROCESS INTEGRATION (1990) Lattice Press, 66-83. **DATE CONSIDERED EXAMINER** LIBC/2825814.1